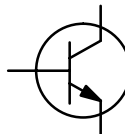


SWITCHMODE™ NPN Silicon Planar Power Transistor

The BUD43B has an application specific state-of-the-art die designed for use in 220 V line operated Switchmode Power supplies and electronic ballast (“light ballast”). The main advantages brought by this new transistor are:

- Improved Efficiency Due to Low Base Drive Requirements:
- High and Flat DC Current Gain h_{FE}
- Fast and Tightened Switching Distributions
- No Coil Required in Base Circuit for Fast Turn-off (no current tail)



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Sustaining Voltage	V_{CEO}	350	Vdc
Collector–Base Breakdown Voltage	V_{CB0}	650	Vdc
Collector–Emitter Breakdown Voltage	V_{CES}	650	Vdc
Emitter–Base Voltage	V_{EBO}	9	Vdc
Collector Current — Continuous	I_C	2	Adc
— Peak (1)	I_{CM}	4	
Base Current — Continuous	I_B	1	Adc
— Peak (1)	I_{BM}	2	
*Total Device Dissipation @ $T_C = 25^\circ\text{C}$	P_D	25	Watt
*Derate above 25°C		0.2	W/ $^\circ\text{C}$
Operating and Storage Temperature	T_J, T_{stg}	-65 to 150	$^\circ\text{C}$

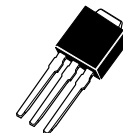
THERMAL CHARACTERISTICS

Thermal Resistance			$^\circ\text{C}/\text{W}$
— Junction to Case	$R_{\theta JC}$	5	
— Junction to Ambient	$R_{\theta JA}$	71.4	
Maximum Lead Temperature for Soldering Purposes: 1/8" from case for 5 seconds	T_L	260	$^\circ\text{C}$

(1) Pulse Test: Pulse Width = 5 ms, Duty Cycle.

BUD43B

POWER TRANSISTORS
2 AMPERES
700 VOLTS
25 WATTS

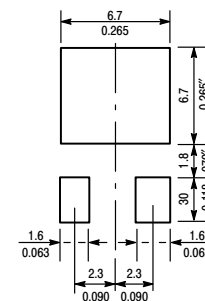


CASE 369-07



CASE 369A-13

MINIMUM PAD SIZES
RECOMMENDED FOR
SURFACE MOUNTED
APPLICATIONS



BUD43B

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Sustaining Voltage ($I_C = 100\text{ mA}$, $L = 25\text{ mH}$)	$V_{CEO(sus)}$	350			Vdc
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CEO}$, $I_B = 0$)	I_{CEO}			100	μA
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CES}$, $V_{BE} = 0$) 125°C	I_{CES}			10 200	μA
Emitter–Cutoff Current ($V_{EB} = 9\text{ Vdc}$, $I_C = 0$)	I_{EBO}			100	μA

ON CHARACTERISTICS

Base–Emitter Saturation Voltage ($I_C = 2\text{ Adc}$, $I_B = 0.5\text{ Adc}$)	$V_{BE(sat)}$			125	Vdc
Collector–Emitter Saturation Voltage ($I_C = 2\text{ Adc}$, $I_B = 0.5\text{ Adc}$)	$V_{CE(sat)}$			1	Vdc
DC Current Gain ($I_C = 1\text{ Adc}$, $V_{CE} = 2\text{ Vdc}$) ($I_C = 2\text{ Adc}$, $V_{CE} = 5\text{ Vdc}$)	h_{FE}			8 6	

DYNAMIC CHARACTERISTICS

Current Gain Bandwidth ($I_C = 0.5\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1\text{ MHz}$)	f_T			13	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1\text{ MHz}$)	C_{ob}			40	pF
Input Capacitance ($V_{EB} = 8\text{ V}$)	C_{ib}			400	pF

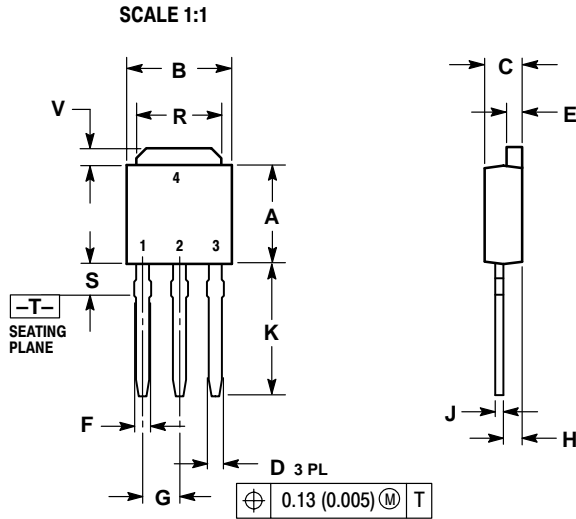
SWITCHING CHARACTERISTICS (Resistive Load) (D.C. $\leq 10\%$, Pulse Width = 20 μs)

Turn–on Time	($I_C = 1.2\text{ Adc}$, $I_{B1} = 0.4\text{ Adc}$, $I_{B2} = 0.1\text{ Adc}$, $V_{CC} = 300\text{ V}$)	@ $T_C = 25^\circ\text{C}$	t_{off}	4.7		5.8	μs
Fall Time	($I_C = 2.5\text{ Adc}$, $I_{B1} = 0.5\text{ Adc}$, $I_{B2} = 0.5\text{ Adc}$, $V_{CC} = 150\text{ V}$)	@ $T_C = 25^\circ\text{C}$	t_f			800	ns

BUD43B

PACKAGE DIMENSIONS

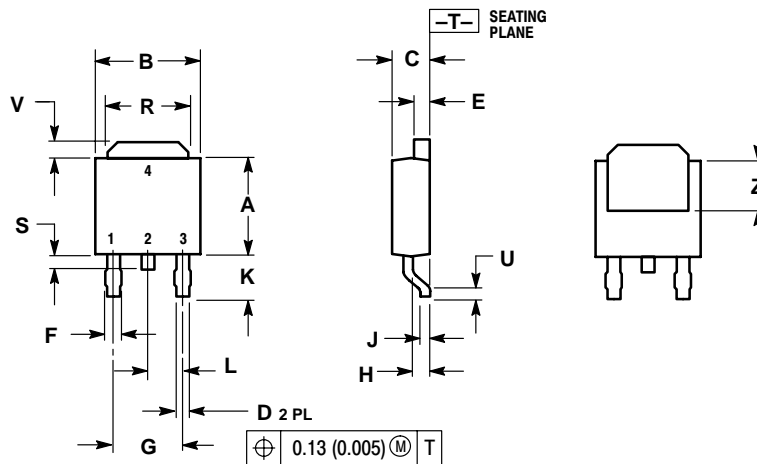
DPAK CASE 369-07 ISSUE M



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.250	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.175	0.215	4.45	5.46
S	0.050	0.090	1.27	2.28
V	0.030	0.050	0.77	1.27

DPAK CASE 369A-13 ISSUE AA



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.250	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.180 BSC		4.58 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29 BSC	
R	0.175	0.215	4.45	5.46
S	0.020	0.050	0.51	1.27
U	0.020	---	0.51	---
V	0.030	0.050	0.77	1.27
Z	0.138	---	3.51	---

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